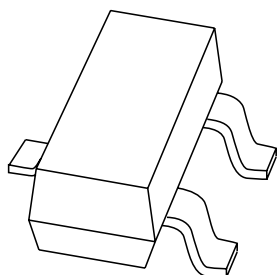


DATA SHEET



MMBT2222A NPN switching transistor

Product specification
Supersedes data of 2000 Apr 11

2004 Jan 16

NPN switching transistor

MMBT2222A

FEATURES

- High current (max. 600 mA)
- Low voltage (max. 40 V).

APPLICATIONS

- Switching and linear amplification.

DESCRIPTION

NPN switching transistor in a SOT23 plastic package.
PNP complement: PMBT2907A.

MARKING

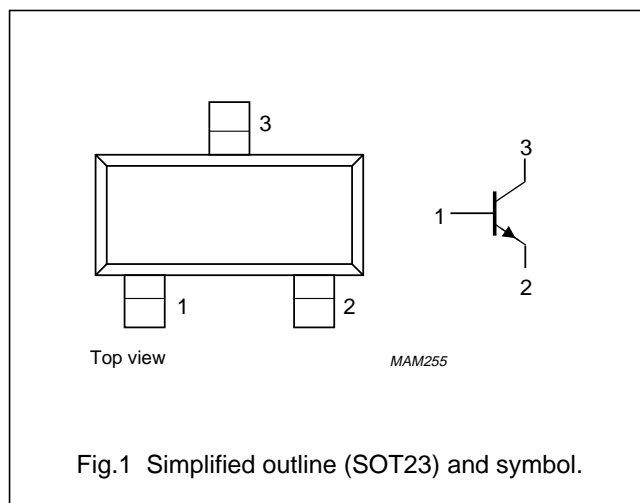
TYPE NUMBER	MARKING CODE ⁽¹⁾
MMBT2222A	7C*

Note

1. * = p : Made in Hong Kong.
 * = t : Made in Malaysia.
 * = W : Made in China.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
MMBT2222A	–	plastic surface mounted package; 3 leads	SOT23

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	75	V
V_{CEO}	collector-emitter voltage	open base	–	40	V
V_{EBO}	emitter-base voltage	open collector	–	6	V
I_C	collector current (DC)		–	600	mA
I_{CM}	peak collector current		–	800	mA
I_{BM}	peak base current		–	200	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ }^{\circ}\text{C}$; note 1	–	250	mW
T_{stg}	storage temperature		–65	+150	$^{\circ}\text{C}$
T_j	junction temperature		–	150	$^{\circ}\text{C}$
T_{amb}	operating ambient temperature		–65	+150	$^{\circ}\text{C}$

Note

1. Transistor mounted on an FR4 printed-circuit board.

NPN switching transistor

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th(j-a)}$	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

$T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

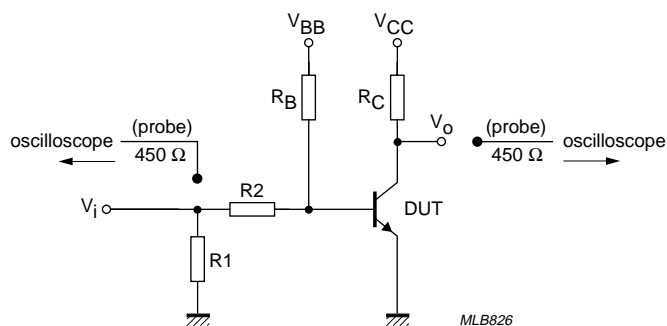
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0$; $V_{CB} = 60\text{ V}$	–	10	nA
		$I_E = 0$; $V_{CB} = 60\text{ V}$; $T_j = 125\text{ }^{\circ}\text{C}$	–	10	μA
I_{EBO}	emitter cut-off current	$I_C = 0$; $V_{EB} = 5\text{ V}$	–	10	nA
h_{FE}	DC current gain	$I_C = 0.1\text{ mA}$; $V_{CE} = 10\text{ V}$	35	–	
		$I_C = 1\text{ mA}$; $V_{CE} = 10\text{ V}$	50	–	
		$I_C = 10\text{ mA}$; $V_{CE} = 10\text{ V}$	75	–	
		$I_C = 10\text{ mA}$; $V_{CE} = 10\text{ V}$; $T_{amb} = -55\text{ }^{\circ}\text{C}$	35	–	
		$I_C = 150\text{ mA}$; $V_{CE} = 10\text{ V}$	100	300	
		$I_C = 150\text{ mA}$; $V_{CE} = 1\text{ V}$	50	–	
		$I_C = 500\text{ mA}$; $V_{CE} = 10\text{ V}$	40	–	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 150\text{ mA}$; $I_B = 15\text{ mA}$; note 1	–	300	mV
		$I_C = 500\text{ mA}$; $I_B = 50\text{ mA}$; note 1	–	1	V
V_{BEsat}	base-emitter saturation voltage	$I_C = 150\text{ mA}$; $I_B = 15\text{ mA}$; note 1	0.6	1.2	V
		$I_C = 500\text{ mA}$; $I_B = 50\text{ mA}$; note 1	–	2	V
C_c	collector capacitance	$I_E = i_e = 0$; $V_{CB} = 10\text{ V}$; $f = 1\text{ MHz}$	–	8	pF
C_e	emitter capacitance	$I_C = i_c = 0$; $V_{EB} = 500\text{ mV}$; $f = 1\text{ MHz}$	–	25	pF
f_T	transition frequency	$I_C = 20\text{ mA}$; $V_{CE} = 20\text{ V}$; $f = 100\text{ MHz}$	300	–	MHz
F	noise figure	$I_C = 100\text{ }\mu\text{A}$; $V_{CE} = 5\text{ V}$; $R_S = 1\text{ k}\Omega$; $f = 1\text{ kHz}$	–	4	dB
Switching times (between 10% and 90% levels); (see Fig.2)					
t_{on}	turn-on time	$I_{Con} = 150\text{ mA}$; $I_{Bon} = 15\text{ mA}$; $I_{Boff} = -15\text{ mA}$	–	35	ns
t_d	delay time		–	15	ns
t_r	rise time		–	20	ns
t_{off}	turn-off time		–	250	ns
t_s	storage time		–	200	ns
t_f	fall time		–	60	ns

Note

1. Pulse test: $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.02$.

NPN switching transistor

MMBT2222A



$V_i = 9.5 \text{ V}$; $T = 500 \text{ } \mu\text{s}$; $t_p = 10 \text{ } \mu\text{s}$; $t_r = t_f \leq 3 \text{ ns}$.
 $R1 = 68 \text{ } \Omega$; $R2 = 325 \text{ } \Omega$; $R_B = 325 \text{ } \Omega$; $R_C = 160 \text{ } \Omega$.
 $V_{BB} = -3.5 \text{ V}$; $V_{CC} = 29.5 \text{ V}$.
 Oscilloscope: input impedance $Z_i = 50 \text{ } \Omega$.

Fig.2 Test circuit for switching times.

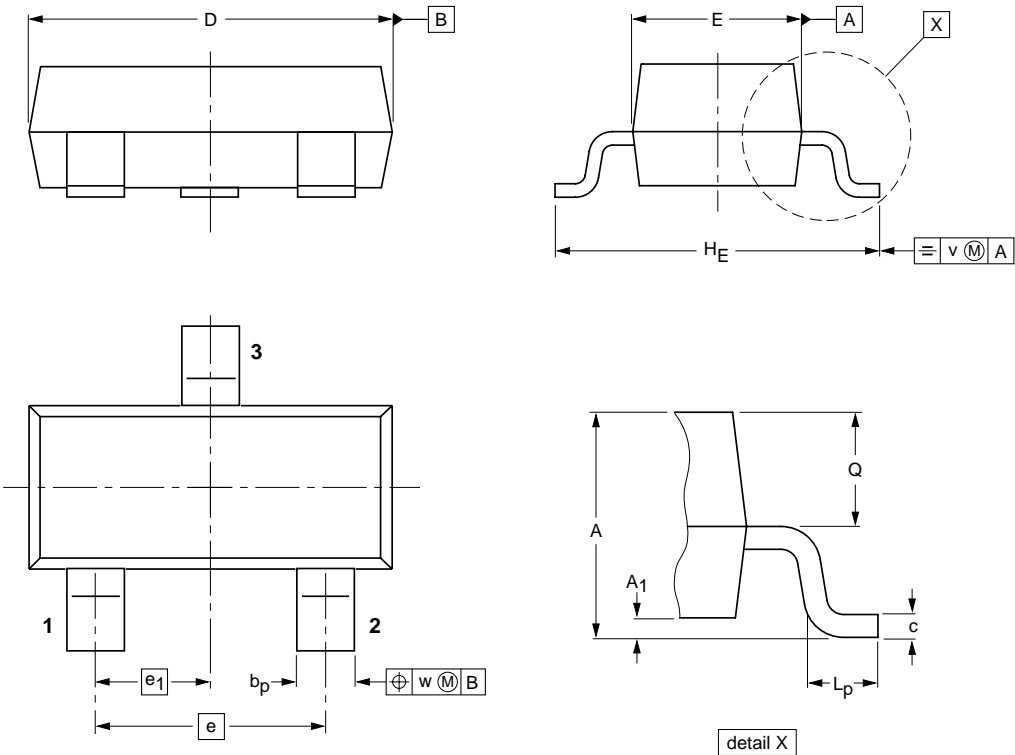
NPN switching transistor

MMBT2222A

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max.	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT23		TO-236AB				97-02-28 99-09-13

NPN switching transistor

MMBT2222A

DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾⁽³⁾	DEFINITION
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Printed in The Netherlands

R75/02/pp7

Date of release: 2004 Jan 16

Document order number: 9397 750 12432

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